

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A method of fabricating a MOS transistor, the method comprising:

 creating a form structure above a starting structure, the form structure having an opening exposing a single portion of the starting structure;

 forming a semiconductor material in the opening of the form structure to create a formed semiconductor body having a single generally planar bottom surface above the starting structure, the formed semiconductor body comprising a first body portion, a second body portion, and a third body portion, the second body portion being disposed between the first and third body portions and having first and second sides and a top;

 removing the form structure;

 forming a gate structure disposed along at least a portion of the top and sides of the second body portion, the gate structure comprising a conductive gate electrode and a gate dielectric disposed between the gate electrode and the second body portion; and

 doping the first and third body portions to form source/drains in the first and third body portions.

2. (Original) The method of claim 1, wherein forming the semiconductor material in the opening of the form structure comprises:

 depositing the semiconductor material over the form structure and in the opening of the form structure; and

 planarizing the semiconductor material to expose the form structure.

3. (Original) The method of claim 2, wherein the starting structure comprises a semiconductor and wherein depositing the semiconductor material comprises depositing epitaxial silicon, epitaxial silicon germanium, epitaxial germanium, or epitaxial gallium arsenide over the form structure and in the opening of the form structure.

4. (Original) The method of claim 2, wherein depositing the semiconductor material comprises depositing epitaxial silicon over the form structure and in the opening of the form structure.

5. (Original) The method of claim 2, wherein the form structure comprises silicon nitride.

6. (Original) The method of claim 1, forming the semiconductor material in the opening of the form structure comprises forming silicon, silicon germanium, germanium, or gallium arsenide in the opening of the form structure.

7. (Original) The method of claim 1, wherein forming the semiconductor material comprises forming silicon in the opening of the form structure.

8. (Original) The method of claim 1, wherein the form structure comprises silicon nitride.

9. (Original) The method of claim 1, wherein creating the form structure comprises:

depositing a form layer material above the starting structure; and
selectively removing portions of the form layer material to create the opening exposing the single portion of the starting structure.

10. (Original) The method of claim 1, wherein forming the gate structure comprises:

forming a gate dielectric material over the formed semiconductor body;
forming a conductive gate electrode material above the gate dielectric
material; and
selectively removing the gate electrode material over the first and third
body portions of the formed semiconductor body to define a gate structure
disposed along at least a portion of the top and sides of the second body portion.

11-24 (cancelled).